Is Now Part of

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor®

April 2017

FNF50560TD1

Motion SPM® 55 Series

Features

- UL Certified No. E209204 (UL1557)
- 600 V - 5 A 3-Phase IGBT Inverter Including Control IC for Gate Drive and Protections
- Low-Loss, Short-Circuit Rated IGBTs
- Built-In Bootstrap Diodes in HVIC
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Active-HIGH interface, works with 3.3 / 5 V Logic, Schmitt-trigger Input
- HVIC for Gate Driving, Under-Voltage and Short-Circuit Current Protection
- Fault Output for Under-Voltage and Short-Circuit Current Protection
- Inter-Lock Function to Prevent Short-Circuit
- Shut-Down Input
- HVIC Temperature-Sensing Built-In for Temperature Monitoring
- Optimized for 15 - 20 kHz Switching Frequenc5.9(ng Fre)14nm

- AN-9097 - SPM® 55 Packing Mounting Guidance

General Description

FNF50560TD1 is a Motion SPM 55 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, inter-lock function, over-current shutdown, thermal monitoring of drive IC, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's robust short-circuit-rated IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.

Figure 1. 3D Package Drawing
(Click to Activate 3D Content)

Package Marking and Ordering Information

Device	Device Marking	Package	Packing Type	Quantity
FNF50560TD1	FNF50560TD1	SPMFA-A20	RAIL	13

Integrated Power Functions

- 600 V - 5 A IGBT inverter for three phase DC / AC power conversion (Please refer to Figure 3)

Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting
  control circuit Under-Voltage Lock-Out (UVLO) protection
- For inverter low-side IGBTs: gate drive circuit, Short-Circuit Protection (SCP)
  control supply circuit Under-Voltage Lock-Out (UVLO) protection
- Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: High-active interface, works with 3.3 / 5 V logic, Schmitt trigger input
- Built in Bootstrap circuitry in HVIC

Pin Configuration

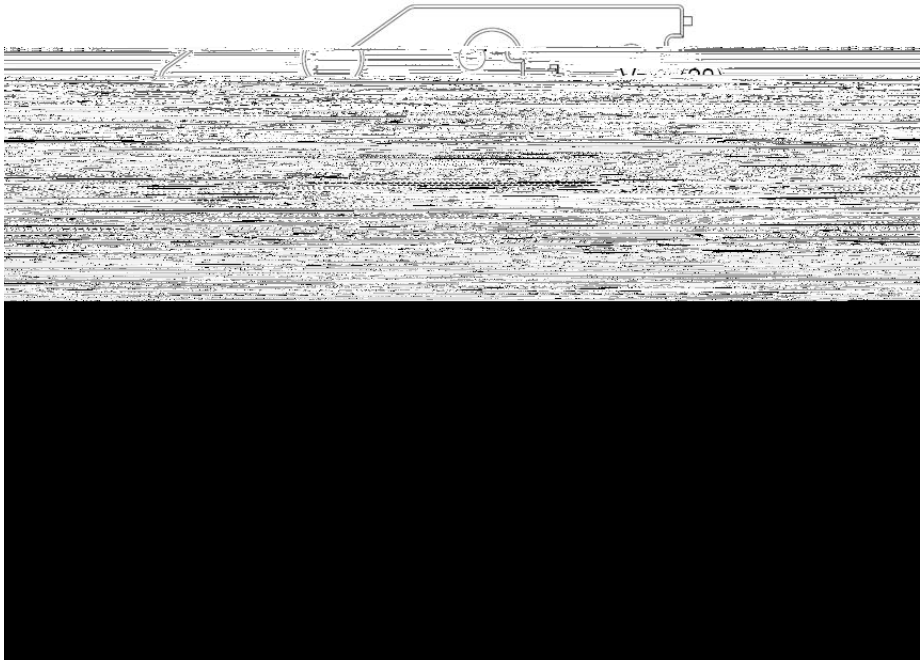


Figure 2. Top View

Pin Descriptions

Pin Number	Pin Name	Pin Description
1	P	Positive DC-Link Input
2	U, V_S(U)	Output for U Phase
3	V, V_S(V)	Output for V Phase
4	W, V_S(W)	Output for W Phase
5	N_U	Negative DC-Link Input for U Phase
4	W, V	

Internal Equivalent Circuit and Input/Output Pins

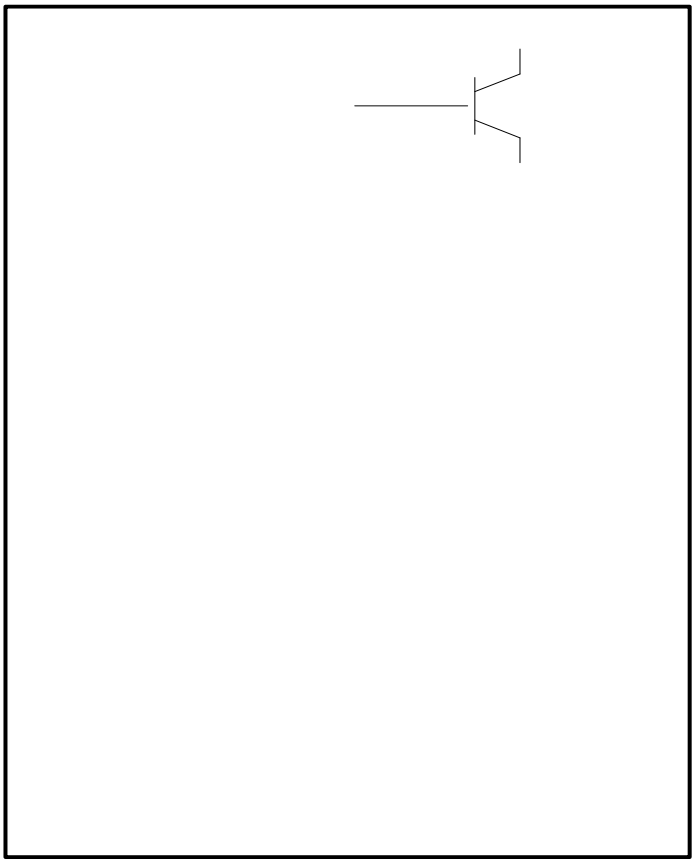


Figure 3. Internal Block Diagram

Note:

1. Inverter high-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT.
2. Inverter low-side is composed of three IGBTs, freewheeling diodes, and one control IC for each IGBT. It has gate drive and protection functions.
3. Single drive IC has gate driver for six IGBTs and protection functions.
4. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.

Absolute Maximum Ratings

Control Part

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
I_{QDD}	Quiescent V_{DD} Supply Current	V_{DD} = 15 V, $IN_{(UH,VH,WH,UL,VL,WL)}$ = 0 V	V_{DD} - COM	-	1.5	2.0	mA
I_{PDD}	Operating V_{DD} Supply Current	V_{DD} = 15 V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input	V_{DD} - COM	-	2.0	2.5	mA
I_{QBS}	Quiescent V_{BS} Supply Current	V_{BS} = 15 V, $IN_{(UH, VH, WH)}$ = 0 V	$V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	-	30	60	μA
I_{PBS}	Operating V_{BS} Supply Current	V_{DD} = V_{BS} = 15 V, f_{PWM} = 20 kHz, duty = 50%, applied to one PWM signal input for high - side	$V_{B(U)}$ - $V_{S(U)}$, $V_{B(V)}$ - $V_{S(V)}$, $V_{B(W)}$ - $V_{S(W)}$	-	500	650	μA
V_{FH}	Fault Output Voltage	V_{SC} = 0 V, V_F Circuit: 10 kΩ to 5 V Pull-up		4.5	-	-	V
V_{FL}		V_{SC} = 1 V, V_F Circuit: 10 kΩ to 5 V Pull-up		-	-	0.5	V
$V_{SC(ref)}$	Short-Circuit Trip Level	V_{DD} = 15 V (Note 4)		0.45	0.5	0.55	V
UV_{DDD}	Supply Circuit Under-Voltage Protection	Detection level		10.7	11.4	12.1	V
UV_{DDR}		Reset level		11.2	12.3	13.0	V
UV_{BSD}		Detection level		10.1	10.8	11.5	V
UV_{BSR}		Reset level		10.7	11.4	12.1	V
I_{FT}	HVIC Temperature Sensing Current	V_{DD} = V_{BS} = 15 V, T_{HVIC} = 25°C		68	81	95	μA
V_{FT}	HVIC Temperature Sensing Voltage	V_{DD} = V_{BS} = 15 V, T_{HVIC} = 25°C, 10 kΩ to 5 V Pull-up (Figure. 5)		4.05	4.19	4.32	V
t_{FOD}	Fault-Out Pulse Width			40	120	-	μs
V_{FSDR}	Shut-down Reset level	Applied between V_F - COM		-	-	2.4	V
V_{FSDD}	Shut-down Detection level			0.8	-	-	V
$V_{IN(ON)}$	ON Threshold Voltage	Applied between $IN_{(UH)}$, $IN_{(VH)}$, $IN_{(WH)}$, $IN_{(UL)}$, $IN_{(VL)}$, $IN_{(WL)}$ - COM		-	-	2.4	V
$V_{IN(OFF)}$	OFF Threshold Voltage			0.8	-	-	V

Note:

9. Short-circuit protection is functioning for all six IGBTs.

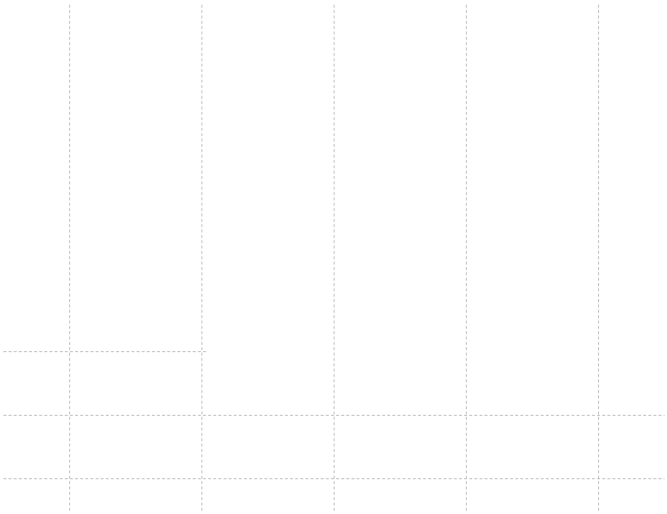


Figure. 5. V-T Curve of Temperature Output of IC (5V pull-up with 10kohm)

Bootstrap Diode Part

Figure 6. Built-In Bootstrap Diode Charatersts

Recommended Operating Conditions

Note:

10. This product might not make response if input pulse width is less than the recommanded value.

Note:

11. RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the SPM 55 product integrates 10 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

Mechanical Characteristics and Ratings

Parameter	Conditions	Min.	Typ.	Max.	Unit
Device Flatness	See Figure 8	-50	-	100	μm
Mounting Torque	Mounting Screw: - M3				

Figure 8. Flatness Measurement Position

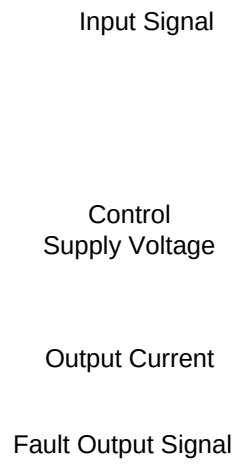
Figure 9. Mounting Screws Torque Order

Note:

12. Do not make over torque when mounting screws. Much mounting torque may cause package cracks, as well as bolts and Al heat-sink destruction.

13. Avoid one side tightening stress. Figure 10 shows the recommended torque order for mounting screws. Uneven mounting can cause the ceramic substrate of the Motion SPM 55 product to be damaged. The Pre-screwing torque is set to 20 ~ 30 % of maximum torque rating.

Time Charts of Protective Function



a1 : Control supply voltage rises: After the voltage rises UV_{DDR}, the circuits start to operate when next input is applied.

a2 : Normal operation: IGBT ON and carrying current.

a3 : Under voltage detection (UV_{DDD}).

a4 : IGBT OFF in spite of control input condition.

a5 : Fault output operation starts.

a6 : Under voltage reset (UV_{DDR}).

a7 : Normal operation: IGBT ON and carrying current.

Figure 10. Under-Voltage Protection (Low-Side)

b1 : Control supply voltage rises: After the voltage reaches UV_{BSR}, the circuits start to operate when next input is applied.

b2 : Normal operation: IGBT ON and carrying current.

b3 : Under voltage detection (UV_{BSD}).

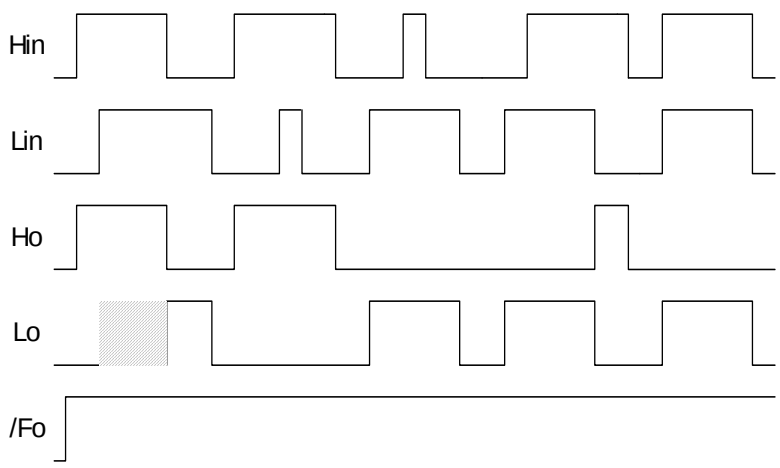
b4 : IGBT OFF in spite of control input condition, but there is no fault output signal.

b5 : Under voltage reset (UV_{BSR})

b6 : Normal operation: IGBT ON and carrying current

Figure 11. Under-Voltage Protection (High-Side)

(with the external shunt resistance and CR connection)



d1 : High Side First - Input - First - Output Mode

d2 : Low Side Noise Mode : No Lo

d3 : High Side Noise Mode : No Ho

d4 : Low Side First - Input - First - Output Mode

d5 : In - Phase Mode : No Ho

Figure 12. Inter-Lock Function

HIN : High-side Input Signal

LIN : Low-side Input Signal

HO : High-Side Output Signal

LO : Low-Side Output Signal

CSC : Short-circuit Current Detection Input

VF : Fault Out Function

Figure 13. Fault-Out Function By Over Current Protection

HIN : High-side Input Signal
LIN : Low-side Input Signal
HO : High-Side Output Signal
LO : Low-Side Output Signal
CSC : Over Current Detection Input
VF : Shutdown Input Function

Figure 14. Shutdown Input Function By External Command

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada.
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

PUBLICATION ORDERING INFORMATION

N. American Technical Support